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[SIHP15N50E-GE3](#)

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www.vishay.com

SiHP15N50E

Vishay Siliconix

## E Series Power MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V) at $T_J$ max.	550
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V 0.243
$Q_g$ max. (nC)	66
$Q_{gs}$ (nC)	8
$Q_{gd}$ (nC)	14
Configuration	Single

### FEATURES

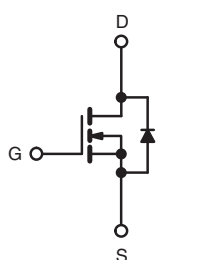
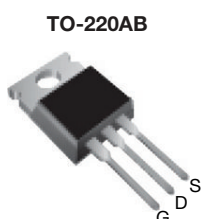
- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Computing
  - PC silver box / ATX power supplies
- Lighting
  - Two stage LED lighting
- Consumer electronics
- Applications using hard switched topologies
  - Power factor correction (PFC)
  - Two switch forward converter
  - Flyback converter
- Switch mode power supplies (SMPS)



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free and Halogen-free	SiHP15N50E-GE3


ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	500	V	
Gate-Source Voltage	$V_{GS}$	$\pm 30$		
Continuous Drain Current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	14.5	A
		$T_C = 100$ °C	9.2	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	28		
Linear Derating Factor		1.25	W/°C	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	136	mJ	
Maximum Power Dissipation	$P_D$	156	W	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C	
Drain-Source Voltage Slope	$dV/dt$	$V_{DS} = 0$ V to 80 % $V_{DS}$	70	V/ns
Reverse Diode $dV/dt$ <sup>d</sup>		27		
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	300	°C	

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 3.1$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.8	



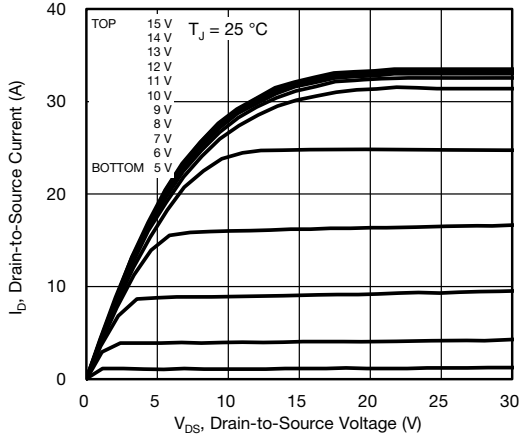
SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$	-	0.62	-	V/ $^\circ\text{C}$
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
		$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 1$	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	25	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}$	-	0.243	0.280	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 7.5\text{ A}$	-	3.9	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	1162	-	pF
Output Capacitance	$C_{oss}$		-	51	-	
Reverse Transfer Capacitance	$C_{rss}$		-	7	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	55	-	
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$		-	164	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}, V_{DS} = 400\text{ V}$	-	33	66	nC
Gate-Source Charge	$Q_{gs}$		-	8	-	
Gate-Drain Charge	$Q_{gd}$		-	14	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 12\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$	-	15	30	ns
Rise Time	$t_r$		-	24	48	
Turn-Off Delay Time	$t_{d(off)}$		-	34	68	
Fall Time	$t_f$		-	18	36	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{ open drain}$	-	0.85	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	14.5	A
Pulsed Diode Forward Current	$I_{SM}$		-	-	28	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 7.5\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 7.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$	-	265	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	3.2	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$		-	23	-	A

**Notes**

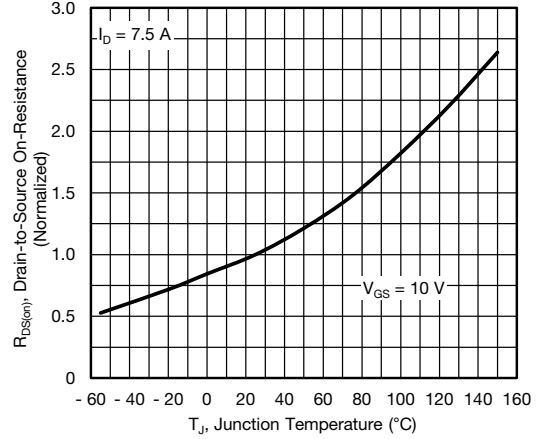
- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .



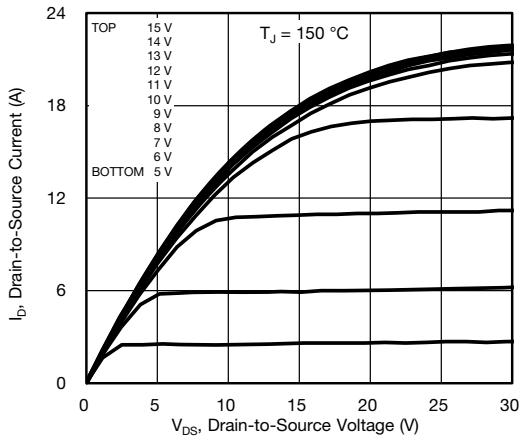
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



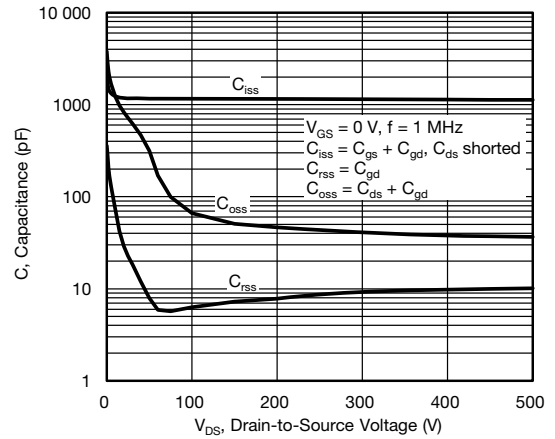
**Fig. 1 - Typical Output Characteristics**



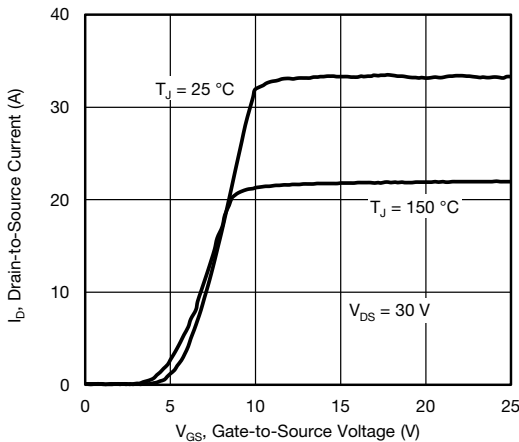
**Fig. 4 - Normalized On-Resistance vs. Temperature**



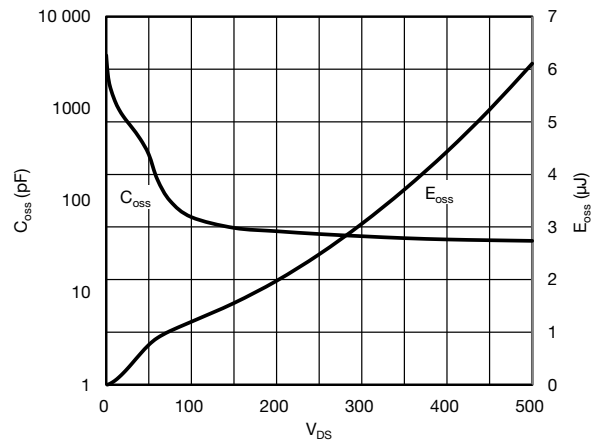
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**

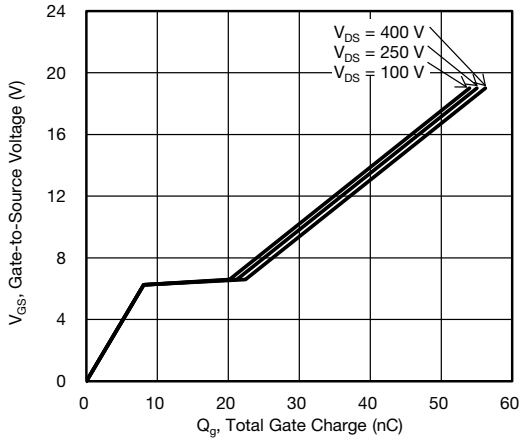


**Fig. 6 - C<sub>oss</sub> and E<sub>oss</sub> vs. V<sub>DS</sub>**

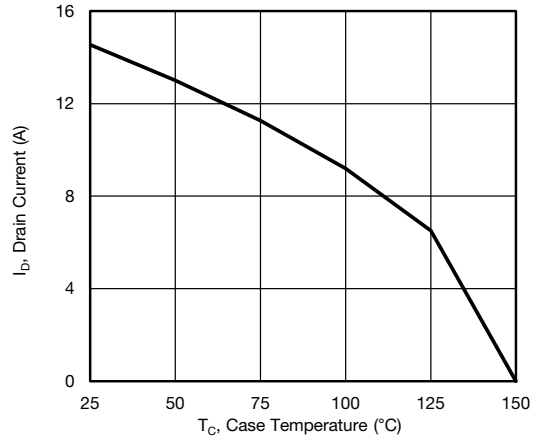


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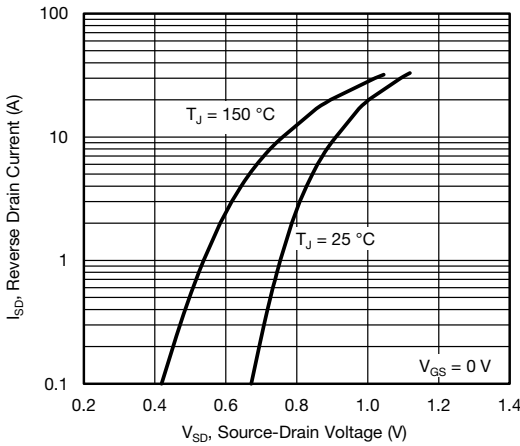
**SIHP15N50E**  
Vishay Siliconix



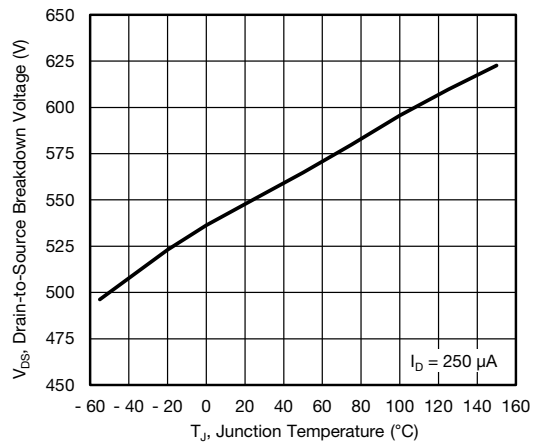
**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**



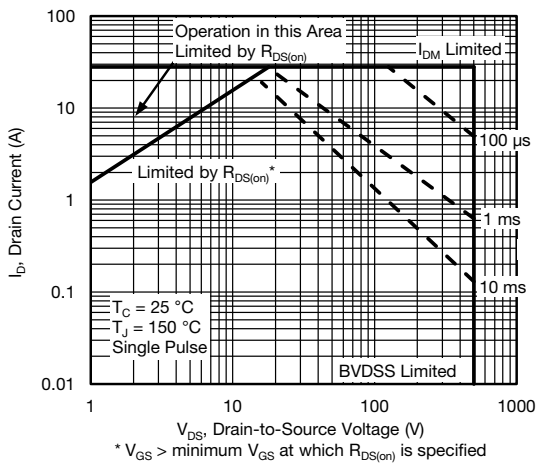
**Fig. 10 - Maximum Drain Current vs. Case Temperature**



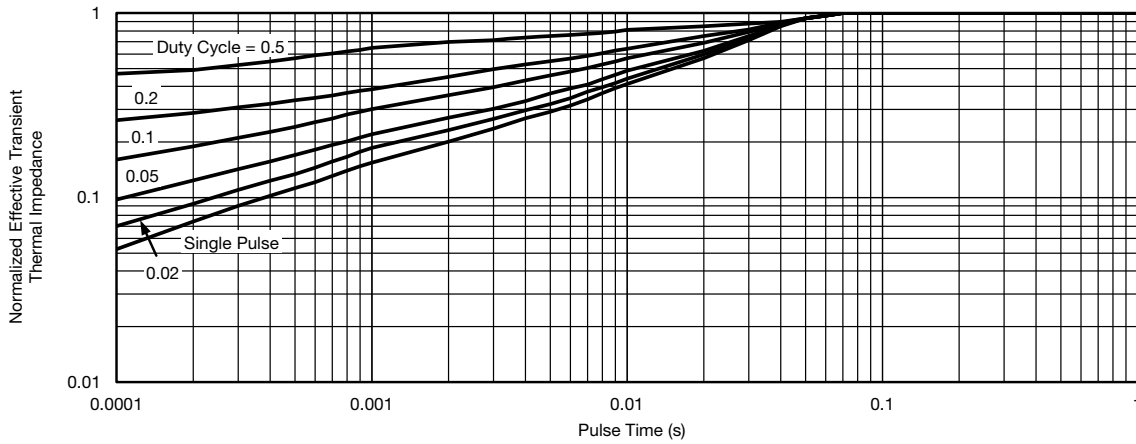
**Fig. 8 - Typical Source-Drain Diode Forward Voltage**



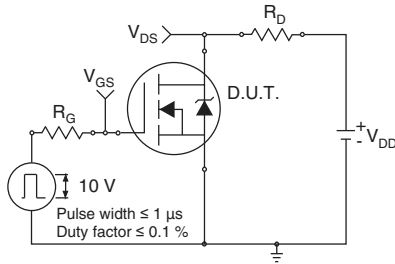
**Fig. 11 - Temperature vs. Drain-to-Source Voltage**



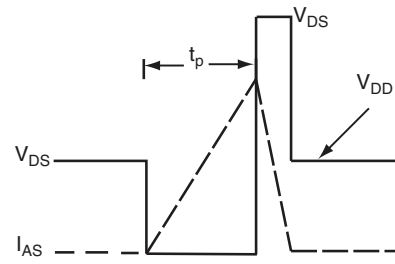
**Fig. 9 - Maximum Safe Operating Area**



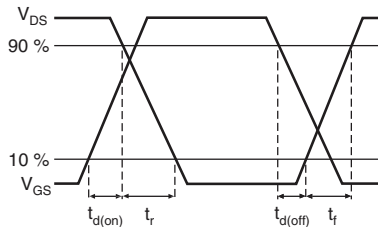
**Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case**



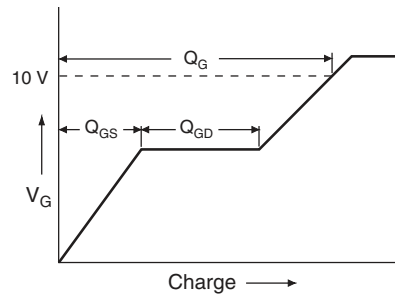
**Fig. 13 - Switching Time Test Circuit**



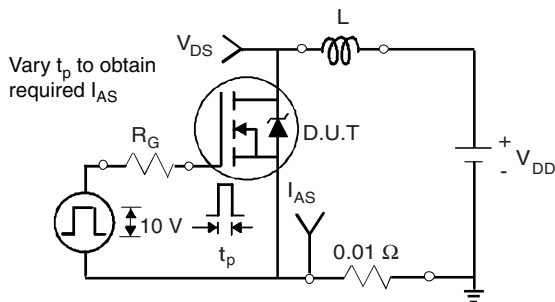
**Fig. 16 - Unclamped Inductive Waveforms**



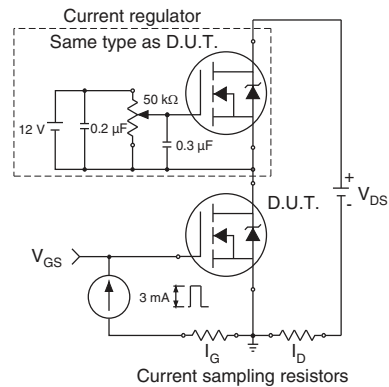
**Fig. 14 - Switching Time Waveforms**



**Fig. 17 - Basic Gate Charge Waveform**

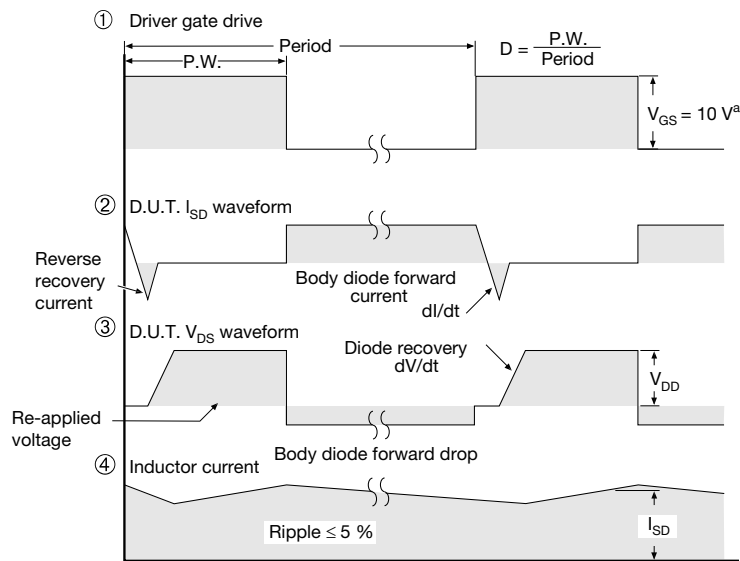
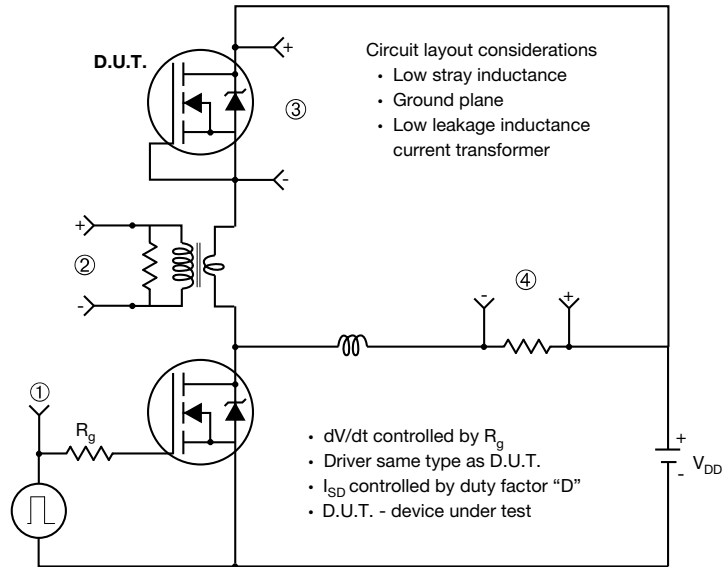


**Fig. 15 - Unclamped Inductive Test Circuit**



**Fig. 18 - Gate Charge Test Circuit**

**Peak Diode Recovery dV/dt Test Circuit**



**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 19 - For N-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91629](http://www.vishay.com/ppg?91629).

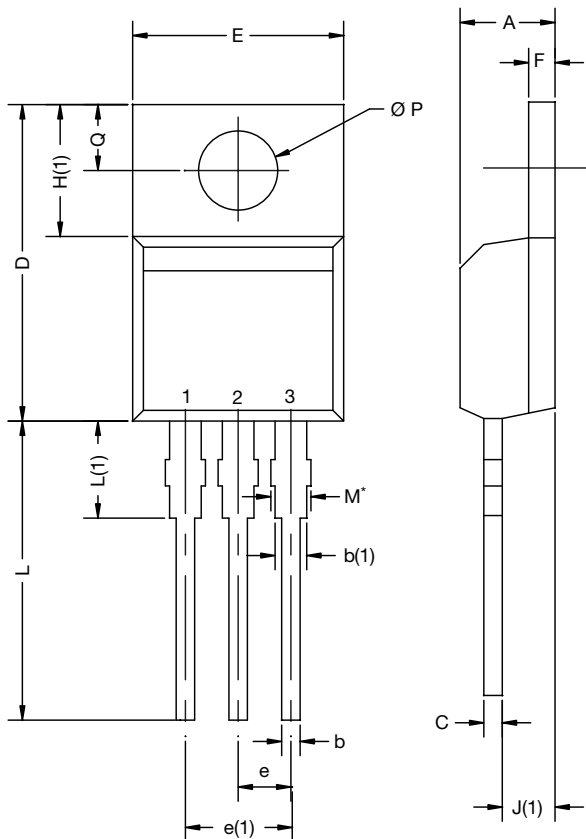


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# Package Information

Vishay Siliconix

## TO-220-1

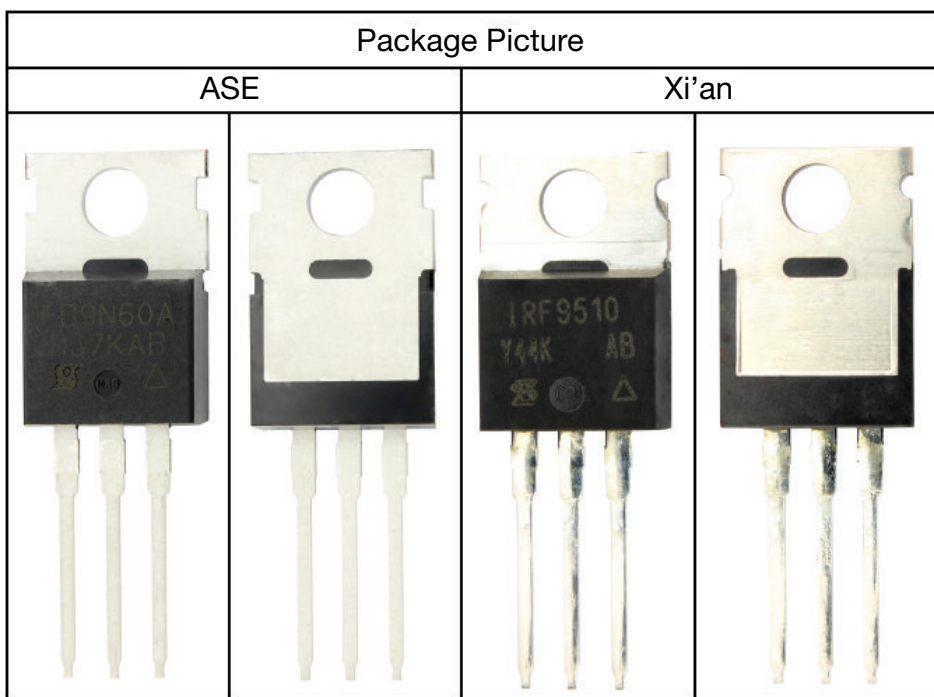


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15  
DWG: 6031

**Note**

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM







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